

ABSTRACT

The present invention provides a bonding material that achieves good bonding strength even when bonding at low temperatures. Flake-shaped silver oxide particles
5 or a silver oxide powder containing the particles are provided. The flake-shaped silver oxide particles have an average thickness of 10 to 100 nm and a D50 of 100 to 350 nm. Moreover, the flake-shaped silver oxide particles or silver oxide powder containing the particles may be used as a paste for bonding a semiconductor substrate with, for example, a power semiconductor chip.

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FIG.1